

This listing of claims will replace all prior versions of the claims in the application:

Listing of Claims:

- 1(Currently amended). A conveyor belt comprising an outer layer (1) and a conveyor-belt base (2), ~~characterized in that~~ wherein the outer layer (1) has been produced via plasma coating.
- 2(Currently amended). The conveyor belt as claimed in claim 1, ~~characterized in that~~ wherein the outer layer (1) comprises an underlayer (3) produced via plasma coating, and adheres by means of this underlayer (3) to the conveyor-belt base (2).
- 3(Currently amended). The conveyor belt as claimed in claim 1 ~~or 2, characterized in that~~ wherein the thickness of the outer layer (1) is in the range from 0.005 to 10 μm .
- 4(Currently amended). The conveyor belt as claimed in claim 2, ~~characterized in that~~ wherein the thickness of the underlayer (3) is from 0.005 to 10 μm .
- 5(Currently amended). A process for production of an outer layer (1) on a conveyor-belt base (2), ~~characterized in that~~ comprising, in the presence of a gaseous monomer capable of excitation in a plasma, the conveyor-belt base (2) is exposed to a plasma in such a way that the gaseous monomer is excited for purposes of plasma coating of the conveyor-belt base (2).
- 6(Currently amended). A process for coating of a conveyor-belt base (2) with an outer layer (1) which comprises an underlayer (3), characterized in that, in the presence of a gaseous monomer capable of excitation in a first plasma, the conveyor-belt base (2) is exposed to a first plasma in such a way that the first gaseous monomer is excited for

purposes of forming an underlayer (3) on the conveyor-belt base (2); and then either
a) in the presence of said first monomer, the underlayer (3) is exposed to a second plasma different from the first plasma in such a way that the first monomer is excited for purposes of plasma coating of the underlayer (3),

or

(b) in the presence of a second gaseous monomer different from the first monomer and capable of excitation in a plasma, the underlayer (3) is exposed to a plasma in such a way that the second monomer is excited for purposes of plasma coating of the underlayer (3).

7(Currently amended). The process as claimed in claim 5 ~~or 6, characterized in that~~ wherein the plasma(s) is/are generated via microwaves whose frequency is from 1 to 10 GHz, or via radio waves whose frequency is from 5 to 30 MHz.

8(Currently amended). The process as claimed in ~~any of the preceding~~ claims 5 to 7, ~~characterized in that~~ wherein the monomer(s) has/have been selected from: ethene; its derivatives substituted with halogen and/or substituted with trifluoromethyl, or its derivatives substituted with π -electron-withdrawing groups; the unbranched or branched alkanes having from 2 to 12 carbon atoms; the cyclic (C₄-C₇) alkanes; the halogenated alkanes, where the halogen atoms have been selected from fluorine and chlorine and where the total calculated from the number of carbon atoms plus the number of fluorine atoms plus twice the number of chlorine atoms is at most 12; the silicon-containing monomers, in particular the (C₃-C₁₀) silanes, (C₄-C₈) siloxanes, or (C₄-C₈) silazanes; acetylene and its derivatives substituted with unbranched or branched, optionally fluorine-substituted alkyl substituents, where the total number of all of the carbon atoms plus all of the fluorine atoms is at most 12; and the iso- or heterocyclic unsubstituted or (C₁-C₄)-alkyl- or (C₂-C₄)-alkenyl-substituted or halogen-substituted aromatics, where the total calculated from the number of carbon atoms plus the number of oxygen atoms plus

the number of nitrogen atoms plus the number of fluorine atoms plus twice the number of sulfur atoms plus twice the number of chlorine atoms is at most 12.

9(Original). The process as claimed in claim 8, characterized in that the monomer(s) is/are selected from tetrafluoroethylene, 1,2-difluoroethylene, acetylene, or hexamethyldisiloxane (HMDSO).

10(Currently amended). The use of an outer layer (~~1~~) produced via plasma coating for increasing the chemicals resistance, solvent resistance, or scratch resistance of a conveyor-belt base (~~2~~), or for reducing the adhesiveness of a conveyor-belt base (~~2~~).

11(New). The conveyor belt as claimed in claim 2, wherein the thickness of the outer layer is in the range from 0.005 to 10 μm .

12(New). The process as claimed in claim 6, wherein the plasma(s) is/are generated via microwaves whose frequency is from 1 to 10 GHz, or via radio waves whose frequency is from 5 to 30 MHz.

13(New). The process as claimed in claim 6, wherein the monomer(s) has/have been selected from: ethene; its derivatives substituted with halogen and/or substituted with trifluoromethyl, or its derivatives substituted with π -electron-withdrawing groups; the unbranched or branched alkanes having from 2 to 12 carbon atoms; the cyclic ($\text{C}_4\text{-C}_7$) alkanes; the halogenated alkanes, where the halogen atoms have been selected from fluorine and chlorine and where the total calculated from the number of carbon atoms plus the number of fluorine atoms plus twice the number of chlorine atoms is at most 12; the silicon-containing monomers, in particular the ($\text{C}_3\text{-C}_{10}$) silanes, ($\text{C}_4\text{-C}_8$) siloxanes, or ($\text{C}_4\text{-C}_8$) silazanes; acetylene and its derivatives substituted with unbranched or branched, optionally fluorine-substituted alkyl substituents, where the total number of all of the carbon atoms plus all of the fluorine atoms is at

most 12; and the iso- or heterocyclic unsubstituted or (C₁-C₄)-alkyl- or (C₂-C₄)-alkenyl-substituted or halogen-substituted aromatics, where the total calculated from the number of carbon atoms plus the number of oxygen atoms plus the number of nitrogen atoms plus the number of fluorine atoms plus twice the number of sulfur atoms plus twice the number of chlorine atoms is at most 12.

14(New). The process as claimed in claim 7, wherein the monomer(s) has/have been selected from: ethene; its derivatives substituted with halogen and/or substituted with trifluoromethyl, or its derivatives substituted with π -electron-withdrawing groups; the unbranched or branched alkanes having from 2 to 12 carbon atoms; the cyclic (C₄-C₇) alkanes; the halogenated alkanes, where the halogen atoms have been selected from fluorine and chlorine and where the total calculated from the number of carbon atoms plus the number of fluorine atoms plus twice the number of chlorine atoms is at most 12; the silicon-containing monomers, in particular the (C₃-C₁₀) silanes, (C₄-C₈) siloxanes, or (C₄-C₈) silazanes; acetylene and its derivatives substituted with unbranched or branched, optionally fluorine-substituted alkyl substituents, where the total number of all of the carbon atoms plus all of the fluorine atoms is at most 12; and the iso- or heterocyclic unsubstituted or (C₁-C₄)-alkyl- or (C₂-C₄)-alkenyl-substituted or halogen-substituted aromatics, where the total calculated from the number of carbon atoms plus the number of oxygen atoms plus the number of nitrogen atoms plus the number of fluorine atoms plus twice the number of sulfur atoms plus twice the number of chlorine atoms is at most 12.